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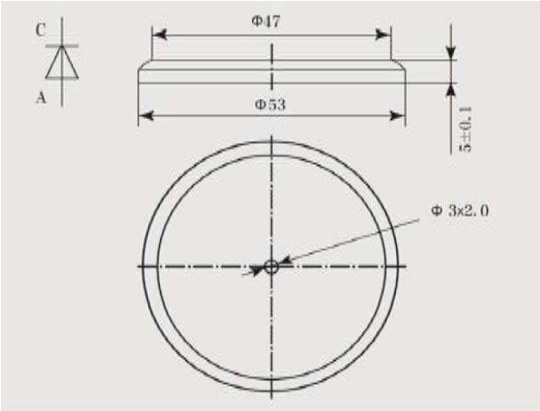
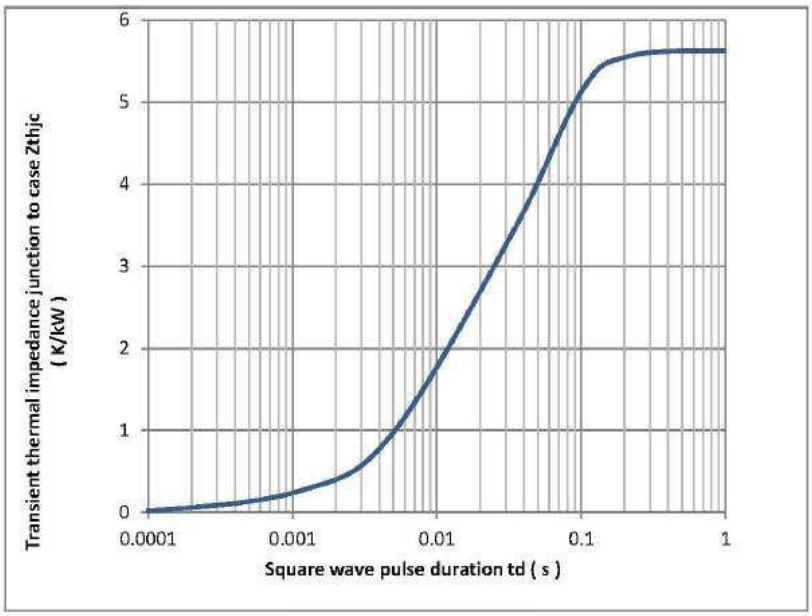
SCD9200

Housingless Diode



Features

- Optimized for high current rectifiers
- Very low threshold voltage and slope resistance
- Very low thermal resistance
- Direct paralleling
- Direct apply 2KHz



Dependence transient thermal impedance junction to case on square pulse

BLOCKING

Symbol	Characteristic	Conditions	Tj (°C)	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	Half sine wave, Tp=10ms f=50Hz		200-400	V
I_{RRM}	Repetitive peak reverse current	V= V_{RRM}	175	50	mA

CONDUCTING

$I_{F(AVM)}$	Mean forward current	Half sine wave, Tc=85°C		9200	A
I_{FRMS}	Max RMS on-state current	Half sine wave, Tc=85°C		11763	A
I_{FSM}	Max peak non-repetitive current	tp=10ms, Tj=175°C Vr~0V		60000	A
I^2t	Max surge current integral			17049K	A^2s
V_F	Maximum on-state voltage	I_F = 8000A	25	0.92÷1.05	V
V_{FO}	Threshold voltage	I_F = 7-21KA	175	0.78	V
r_F	Forward slope resistance	I_F = 7-21KA	175	0.031	mΩ

MOUNTING

$R_{th(j-c)}$	Thermal impedance, sin 180°	Junction to case		≤5.6K	K/W
$R_{th(c-h)}$	Thermal impedance	Case to heatsink		≤2.8K	K/W
T_j	Max. junction temperature			-40 175	°C
T_{stg}	Storage temperature			-40 175	°C
M	Mounting torque			30÷50	KN
W	Weight (Approx.)			100	g

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